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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104bcdfp-v0

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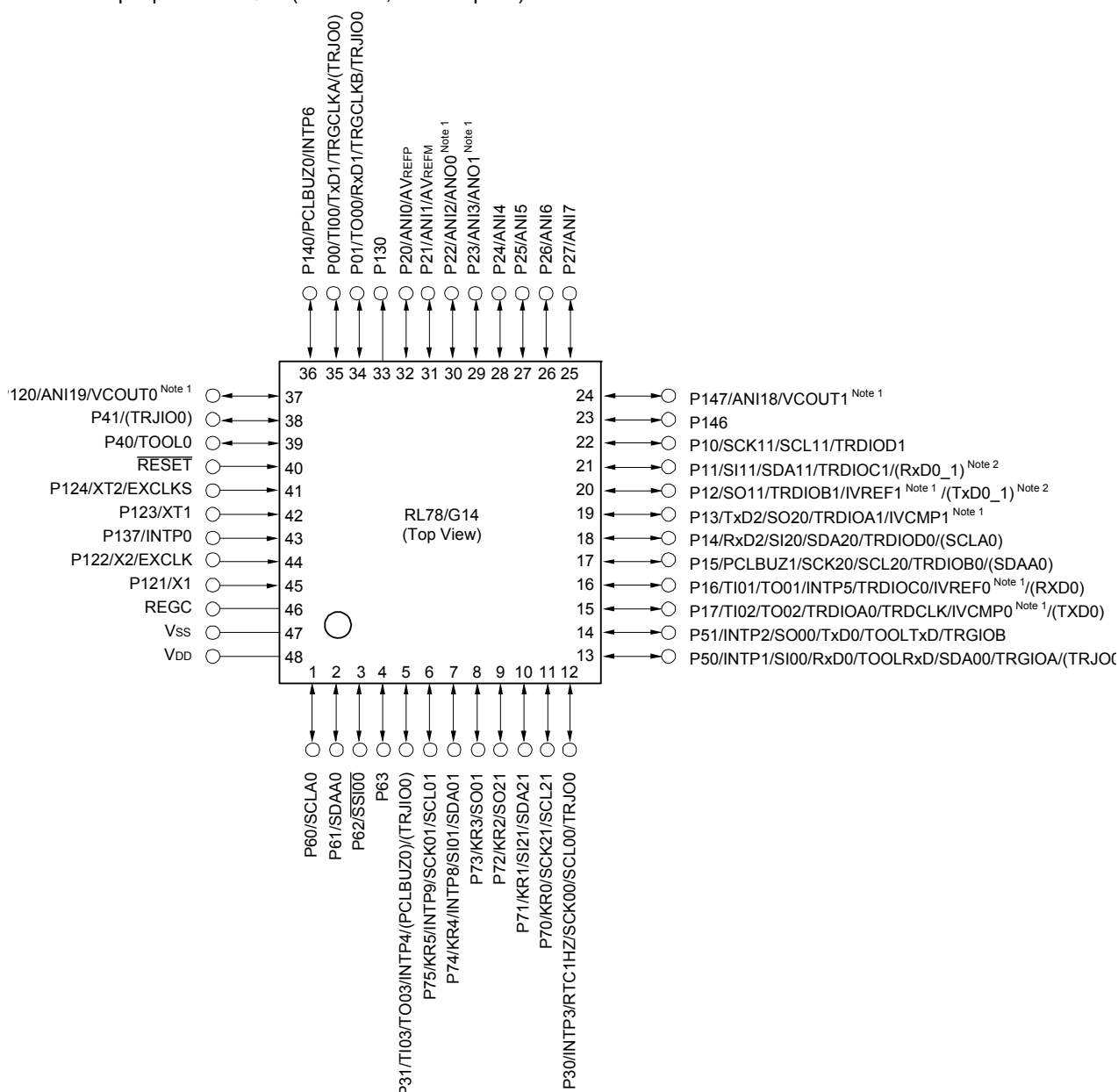
Pin count	Package	Fields of Application Note	Ordering Part Number
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	A	R5F104EAANA#U0, R5F104ECANA#U0, R5F104EDANA#U0, R5F104EEANA#U0, R5F104EFANA#U0, R5F104EGANA#U0, R5F104EHANA#U0 R5F104EAANA#W0, R5F104ECANA#W0, R5F104EDANA#W0, R5F104EEANA#W0, R5F104EFANA#W0, R5F104EGANA#W0, R5F104EHANA#W0
		D	R5F104EADNA#U0, R5F104ECDNA#U0, R5F104EDDNA#U0, R5F104EEDNA#U0, R5F104EFDNA#U0, R5F104EGDNA#U0, R5F104EHDNA#U0 R5F104EADNA#W0, R5F104ECDNA#W0, R5F104EDDNA#W0, R5F104EEDNA#W0, R5F104EFDNA#W0, R5F104EGDNA#W0, R5F104EHDNA#W0
		G	R5F104EAGNA#U0, R5F104ECGNA#U0, R5F104EDGNA#U0, R5F104EEGNA#U0, R5F104EFGNA#U0, R5F104EGGNA#U0, R5F104EHGNA#U0 R5F104EAGNA#W0, R5F104ECGNA#W0, R5F104EDGNA#W0, R5F104EEGNA#W0, R5F104EFGNA#W0, R5F104EGGNA#W0, R5F104EHGNA#W0
44 pins	44-pin plastic LQFP (10 × 10, 0.8 mm pitch)	A	R5F104FAAFP#V0, R5F104FCAFP#V0, R5F104FDAFP#V0, R5F104FEAFP#V0, R5F104FFAFP#V0, R5F104FGAFP#V0, R5F104FHAFP#V0, R5F104FJAFP#V0 R5F104FAAFP#X0, R5F104FCAFP#X0, R5F104FDAFP#X0, R5F104FEAFP#X0, R5F104FFAFP#X0, R5F104FGAFP#X0, R5F104FHAFP#X0, R5F104FJAFP#X0
		D	R5F104FADFP#V0, R5F104FCDFP#V0, R5F104FDDFP#V0, R5F104FEDFP#V0, R5F104FFDFP#V0, R5F104FGDFP#V0, R5F104FHDFP#V0, R5F104FJDFP#V0 R5F104FADFP#X0, R5F104FCDFP#X0, R5F104FDDFP#X0, R5F104FEDFP#X0, R5F104FFDFP#X0, R5F104FGDFP#X0, R5F104FHDFP#X0, R5F104FJDFP#X0
		G	R5F104FAGFP#V0, R5F104FCGFP#V0, R5F104FDGFP#V0, R5F104FEGFP#V0, R5F104FFGFP#V0, R5F104FGGFP#V0, R5F104FHGFP#V0, R5F104FJGFP#V0 R5F104FAGFP#X0, R5F104FCGFP#X0, R5F104FDGFP#X0, R5F104FEGFP#X0, R5F104FFGFP#X0, R5F104FGGFP#X0, R5F104FHGFP#X0, R5F104FJGFP#X0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.6 48-pin products

- 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

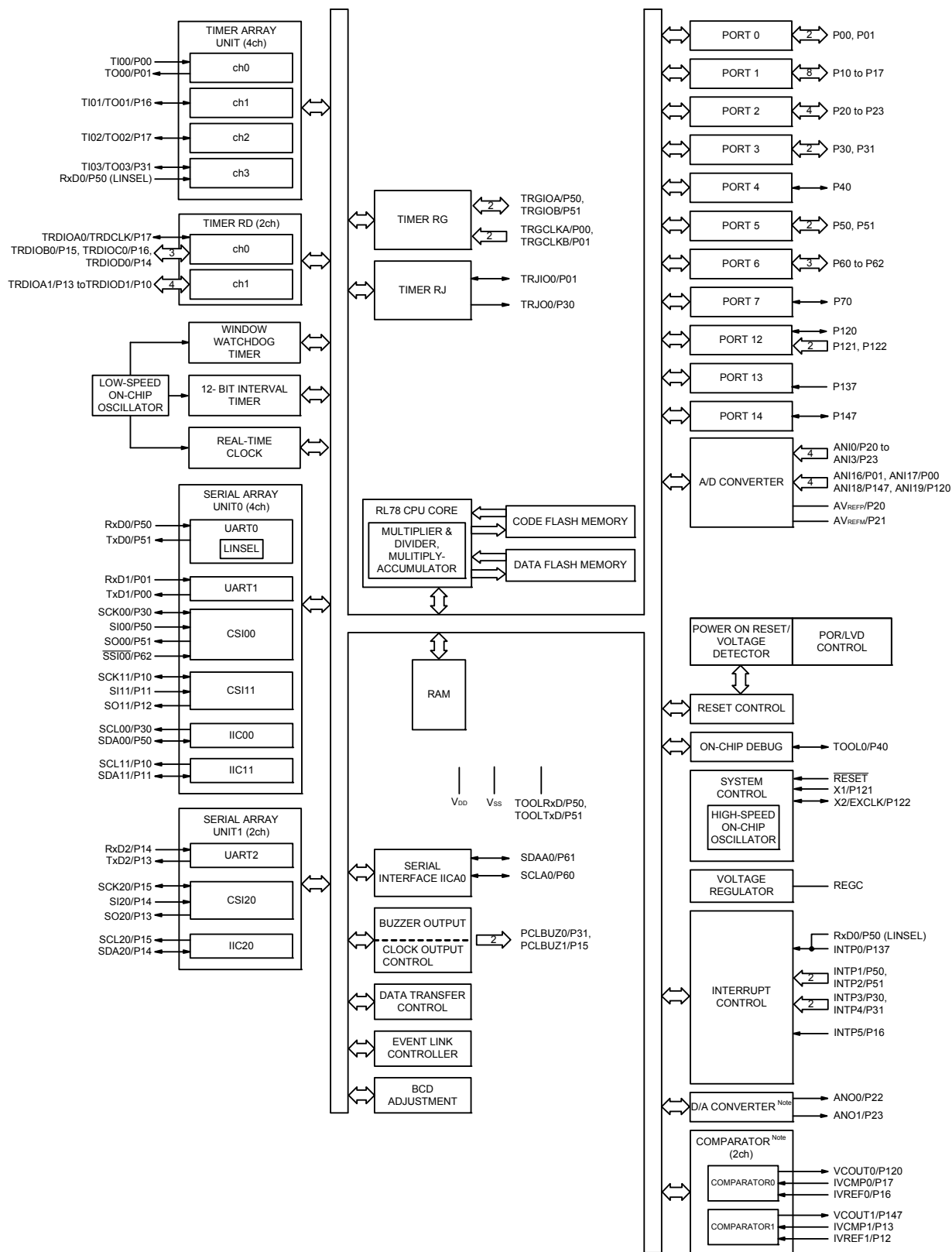
Note 2. Mounted on the 384 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see 1.4 Pin Identification.

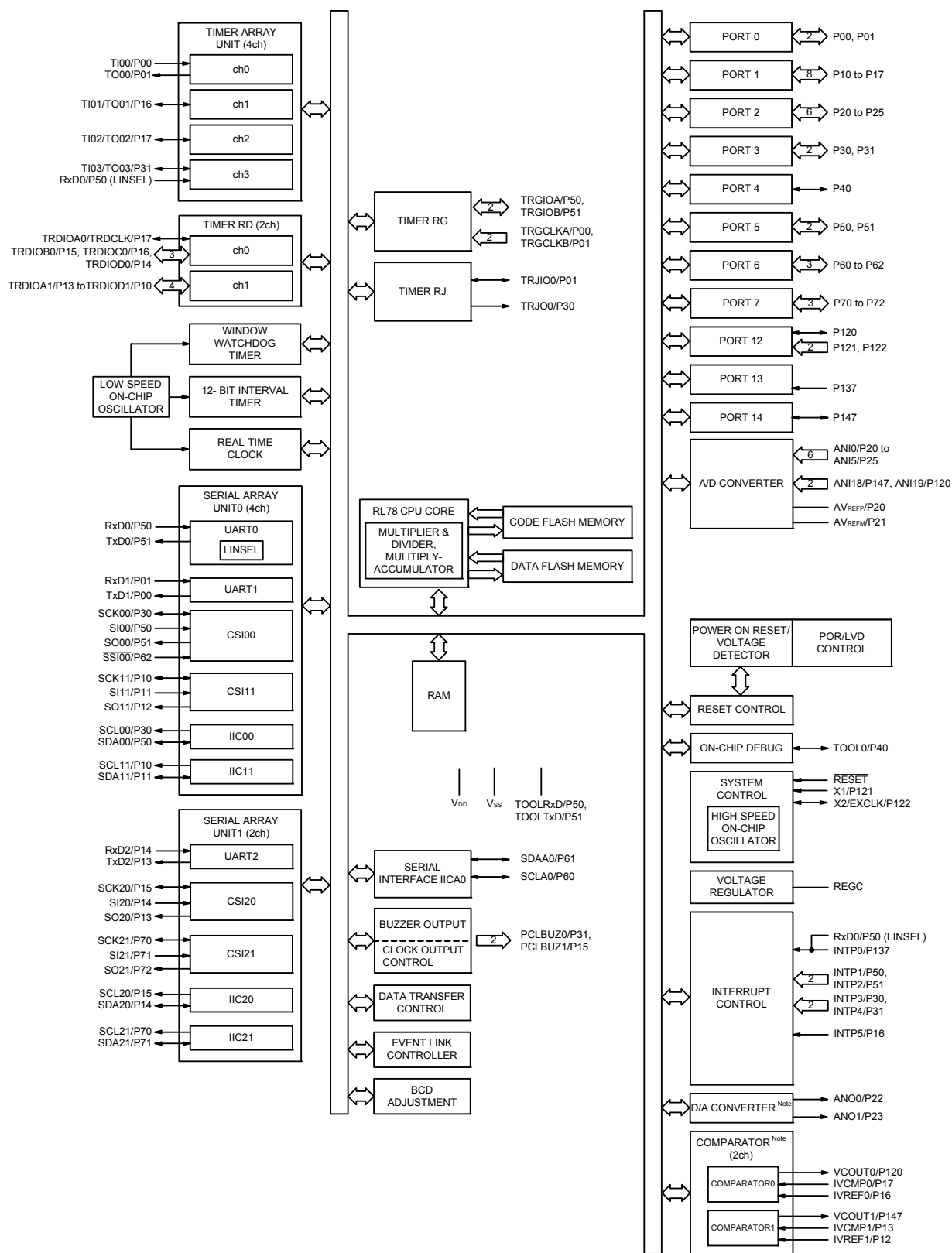
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.5.2 32-pin products



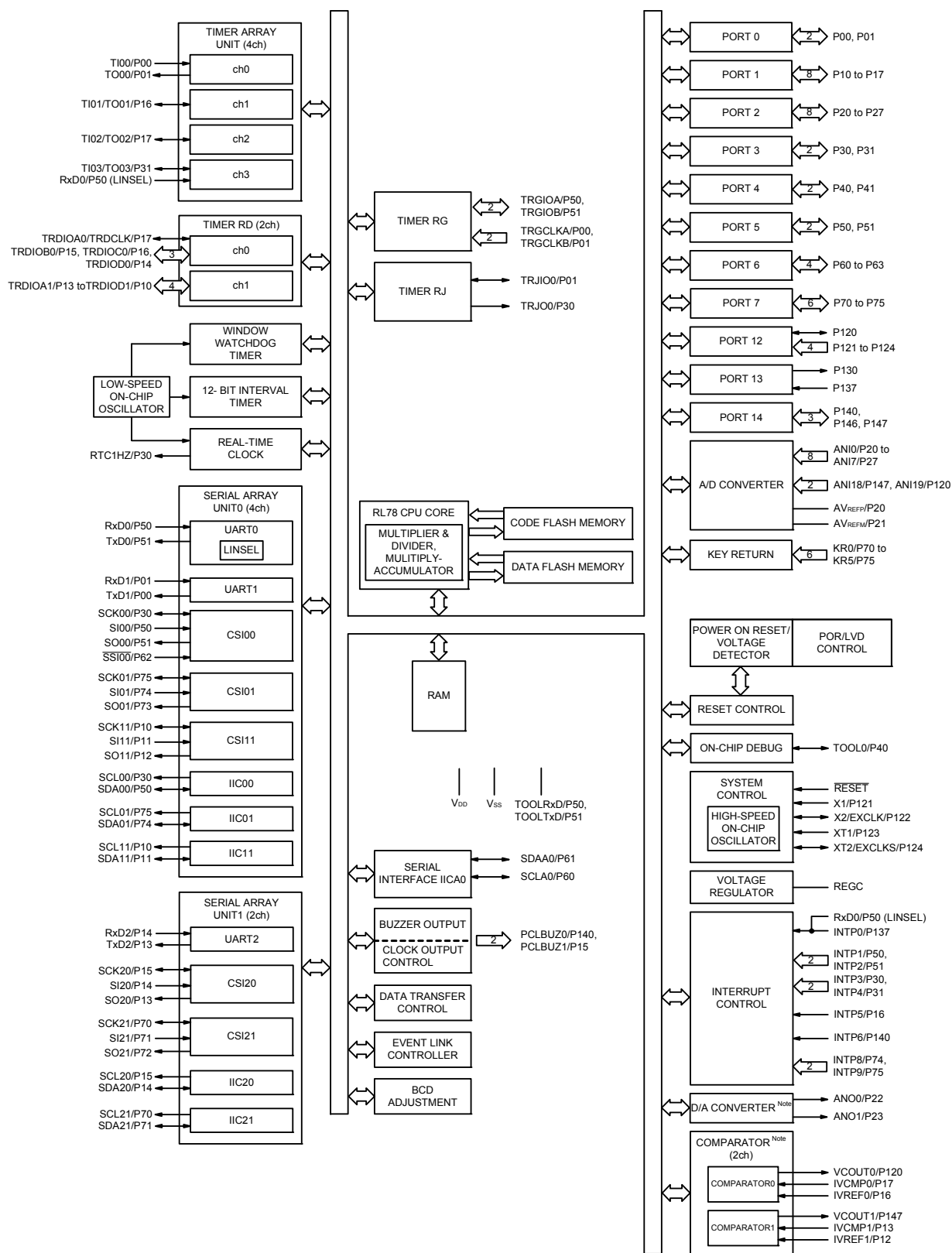
Note Mounted on the 96 KB or more code flash memory products.

1.5.3 36-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.6 48-pin products



Note Mounted on the 96 KB or more code flash memory products.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xD (x = A to C, E to G, J, L): Start address FE900H
R5F104xE (x = A to C, E to G, J, L): Start address FE900H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILI _{H1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V _I = EV _{DD0}				1 μA
	ILI _{H2}	P20 to P27, P137, P150 to P156, <u>RESET</u>	V _I = V _{DD}				1 μA
	ILI _{H3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V _I = V _{DD}	In input port or external clock input			1 μA
				In resonator connection			10 μA
Input leakage current, low	ILI _{L1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V _I = EV _{SS0}				-1 μA
	ILI _{L2}	P20 to P27, P137, P150 to P156, <u>RESET</u>	V _I = V _{SS}				-1 μA
	ILI _{L3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V _I = V _{SS}	In input port or external clock input			-1 μA
				In resonator connection			-10 μA
On-chip pull-up resistance	R _U	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V _I = EV _{SS0} , In input port		10	20	100 kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit			
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{HOCO} = 64 MHz, f _{IH} = 32 MHz Note 4	V _{DD} = 5.0 V		0.79	3.32	mA			
					V _{DD} = 3.0 V		0.79	3.32				
				f _{HOCO} = 32 MHz, f _{IH} = 32 MHz Note 4	V _{DD} = 5.0 V		0.49	2.63				
					V _{DD} = 3.0 V		0.49	2.63				
				f _{HOCO} = 48 MHz, f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.62	2.57				
					V _{DD} = 3.0 V		0.62	2.57				
				f _{HOCO} = 24 MHz, f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.4	2.00				
					V _{DD} = 3.0 V		0.4	2.00				
				f _{HOCO} = 16 MHz, f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.38	1.49				
					V _{DD} = 3.0 V		0.38	1.49				
			LS (low-speed main) mode Note 7	f _{HOCO} = 8 MHz, f _{IH} = 8 MHz Note 4	V _{DD} = 3.0 V		250	800	μA			
					V _{DD} = 2.0 V		250	800				
			LV (low-voltage main) mode Note 7	f _{HOCO} = 4 MHz, f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V		420	755	μA			
					V _{DD} = 2.0 V		420	755				
			HS (high-speed main) mode Note 7	f _{MX} = 20 MHz Note 3, V _{DD} = 5.0 V	Square wave input		0.30	1.63	mA			
						Resonator connection		0.40		1.85		
					f _{MX} = 20 MHz Note 3, V _{DD} = 3.0 V	Square wave input		0.30		1.63		
						Resonator connection		0.40		1.85		
					f _{MX} = 10 MHz Note 3, V _{DD} = 5.0 V	Square wave input		0.20		0.89		
						Resonator connection		0.25		0.97		
					f _{MX} = 10 MHz Note 3, V _{DD} = 3.0 V	Square wave input		0.20		0.89		
						Resonator connection		0.25		0.97		
					LS (low-speed main) mode Note 7	f _{MX} = 8 MHz Note 3, V _{DD} = 3.0 V	Square wave input			110	580	μA
							Resonator connection			140	630	
			f _{MX} = 8 MHz Note 3, V _{DD} = 2.0 V	Square wave input			110	580				
				Resonator connection			140	630				
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 5, T _A = -40°C	Square wave input		0.28	0.66	μA			
					Resonator connection		0.47	0.85				
				f _{SUB} = 32.768 kHz Note 5, T _A = +25°C	Square wave input		0.34	0.66				
					Resonator connection		0.53	0.85				
				f _{SUB} = 32.768 kHz Note 5, T _A = +50°C	Square wave input		0.37	2.35				
					Resonator connection		0.56	2.54				
				f _{SUB} = 32.768 kHz Note 5, T _A = +70°C	Square wave input		0.61	4.08				
					Resonator connection		0.80	4.27				
				f _{SUB} = 32.768 kHz Note 5, T _A = +85°C	Square wave input		1.55	8.09				
					Resonator connection		1.74	8.28				
			I _{DD3} Note 6	STOP mode Note 8	T _A = -40°C					0.19	0.57	μA
					T _A = +25°C					0.25	0.57	
					T _A = +50°C					0.33	2.26	
					T _A = +70°C					0.52	3.99	
					T _A = +85°C					1.46	8.00	

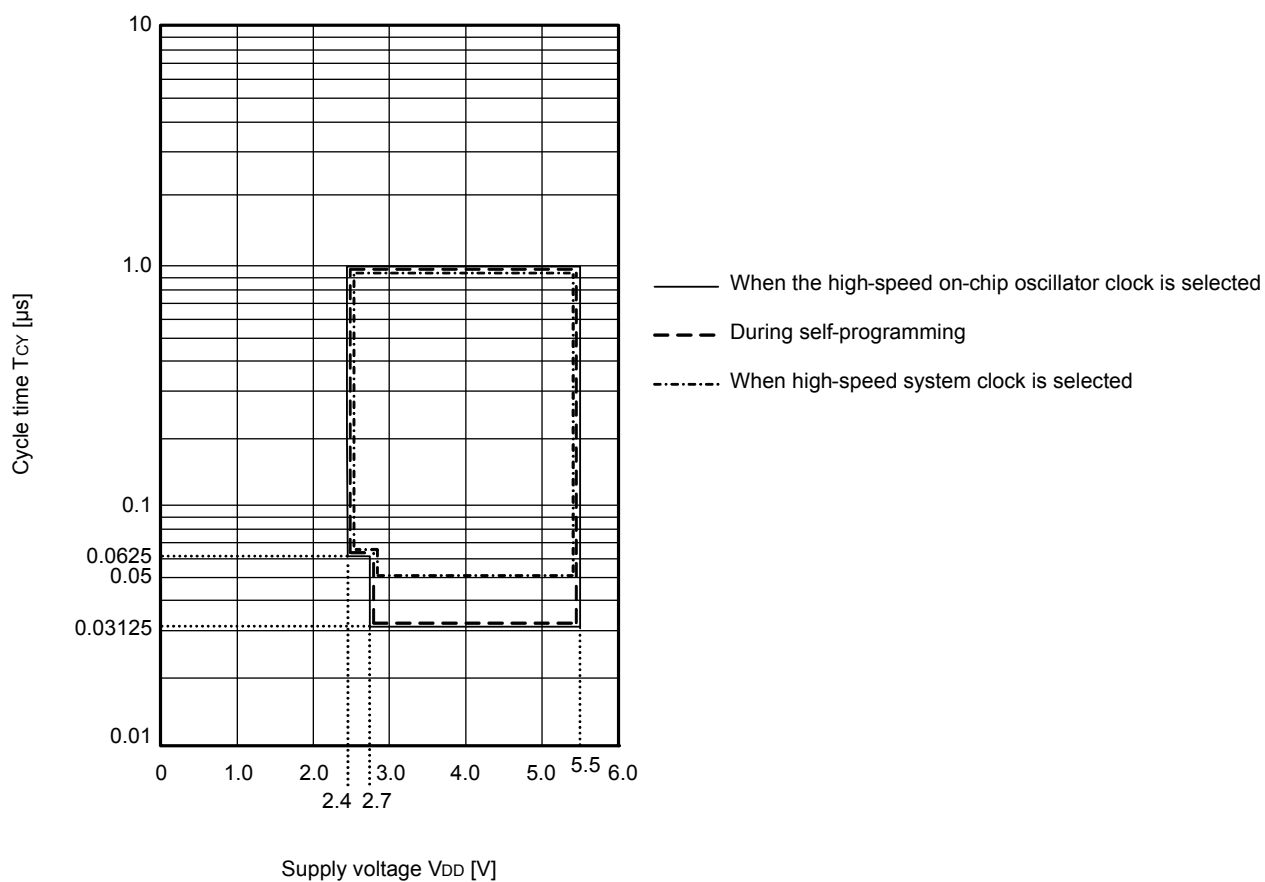
(Notes and Remarks are listed on the next page.)

(4) Peripheral Functions (Common to all products)**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	IFIL Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IIIT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	IWDIT Notes 1, 2, 5	fIL = 15 kHz			0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
D/A converter operating current	IDAC Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating current	ICMP Notes 1, 12, 13	VDD = 5.0 V, Regulator output voltage = 2.1 V	Window mode		12.5		μA
			Comparator high-speed mode		6.5		μA
			Comparator low-speed mode		1.7		μA
		VDD = 5.0 V, Regulator output voltage = 1.8 V	Window mode		8.0		μA
			Comparator high-speed mode		4.0		μA
			Comparator low-speed mode		1.3		μA
LVD operating current	ILVD Notes 1, 7				0.08		μA
Self-programming operating current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	IBGO Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	1.44	
		CSI/UART operation			0.70	0.84	
		DTC operation			3.10		

Note 1. Current flowing to VDD.**Note 2.** When high speed on-chip oscillator and high-speed system clock are stopped.**Note 3.** Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.**Note 4.** Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.

Minimum Instruction Execution Time during Main System Clock Operation

T_{CY} vs V_{DD} (HS (high-speed main) mode)

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	2.7 V ≤ EVDD0 ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		1000		1000		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 12		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 18		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 38		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		ns
Slp setup time (to SCKp↑) Note 1	t _{SIK1}	4.0 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		110		110		110		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		220		220		220		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		220		220		ns
Slp hold time (from SCKp↑) Note 2	t _{KSI1}	1.7 V ≤ EVDD0 ≤ 5.5 V		19		19		19		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	t _{KSO1}	1.7 V ≤ EVDD0 ≤ 5.5 V C = 30 pF Note 4			25		25		25	ns
		1.6 V ≤ EVDD0 ≤ 5.5 V C = 30 pF Note 4			—		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

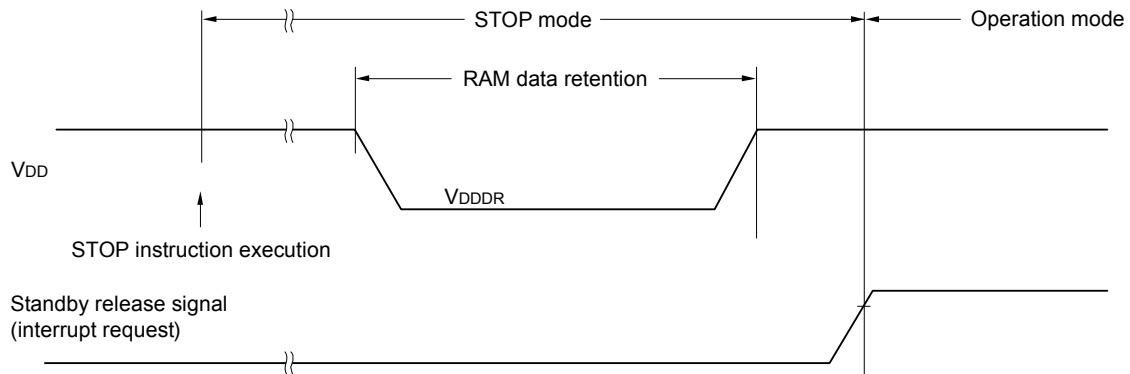
Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

2.7 RAM Data Retention Characteristics

(TA = -40 to +85°C, VSS = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

(TA = -40 to +85°C, 1.8 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fCLK	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C _{erwr}	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

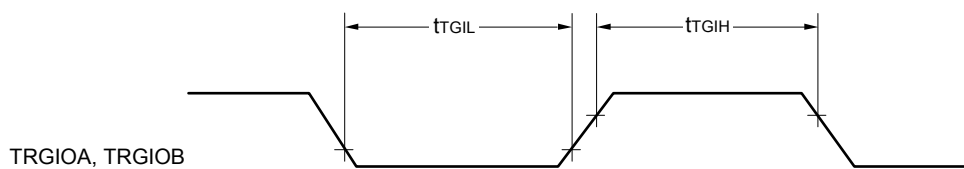
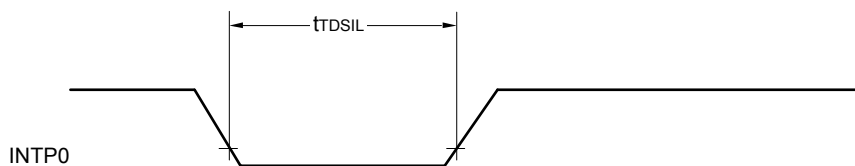
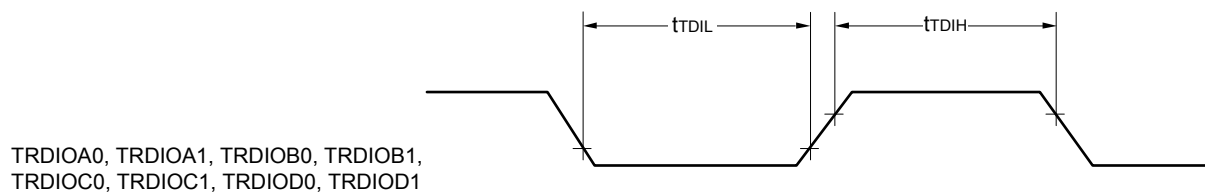
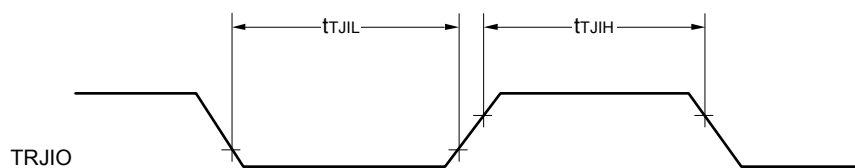
(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

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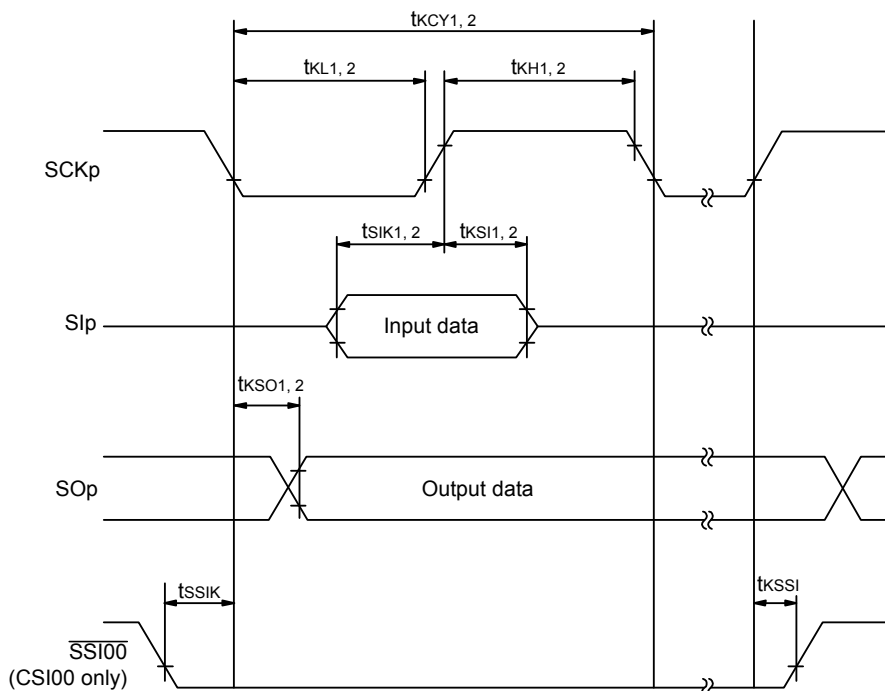
Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage, high	VOH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA		EVDD0 - 0.7	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -2.0 mA		EVDD0 - 0.6	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -1.5 mA		EVDD0 - 0.5	V
	VOH2	P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA		VDD - 0.5	V
Output voltage, low	VOL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 8.5 mA		0.7	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 3.0 mA		0.6	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 1.5 mA		0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 0.6 mA		0.4	V
	VOL2	P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V, IOL2 = 400 μA		0.4	V
	VOL3	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA		2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 5.0 mA		0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA		0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 2.0 mA		0.4	V

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

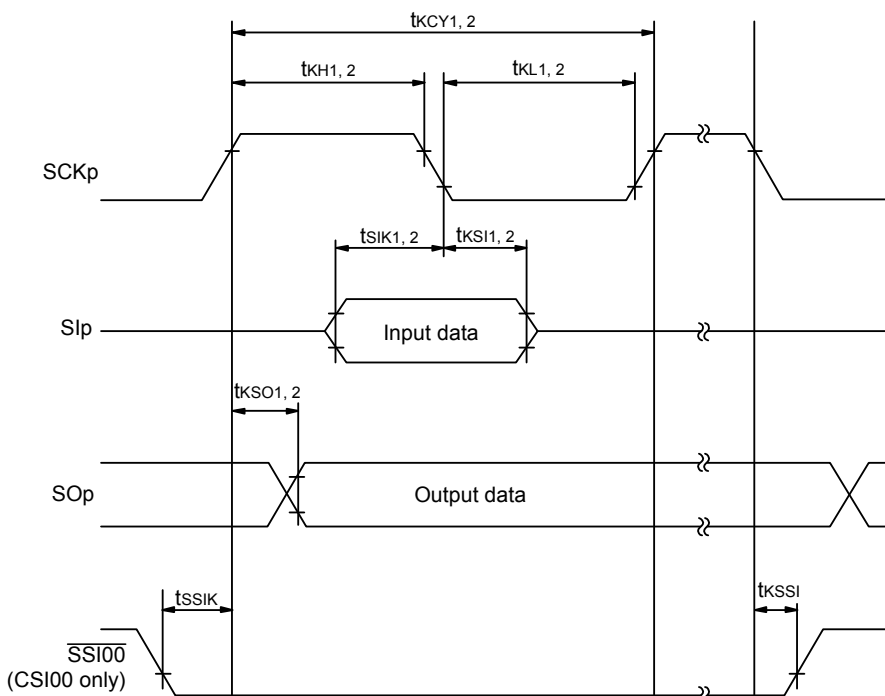
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI16 to ANI20

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$,

$V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target ANI pin: ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.35	%FSR
Full-scale error Notes 1, 2	E_{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI16 to ANI20		0		AV_{REFP} and EV_{DD0}	V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EV_{DD0} \leq AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

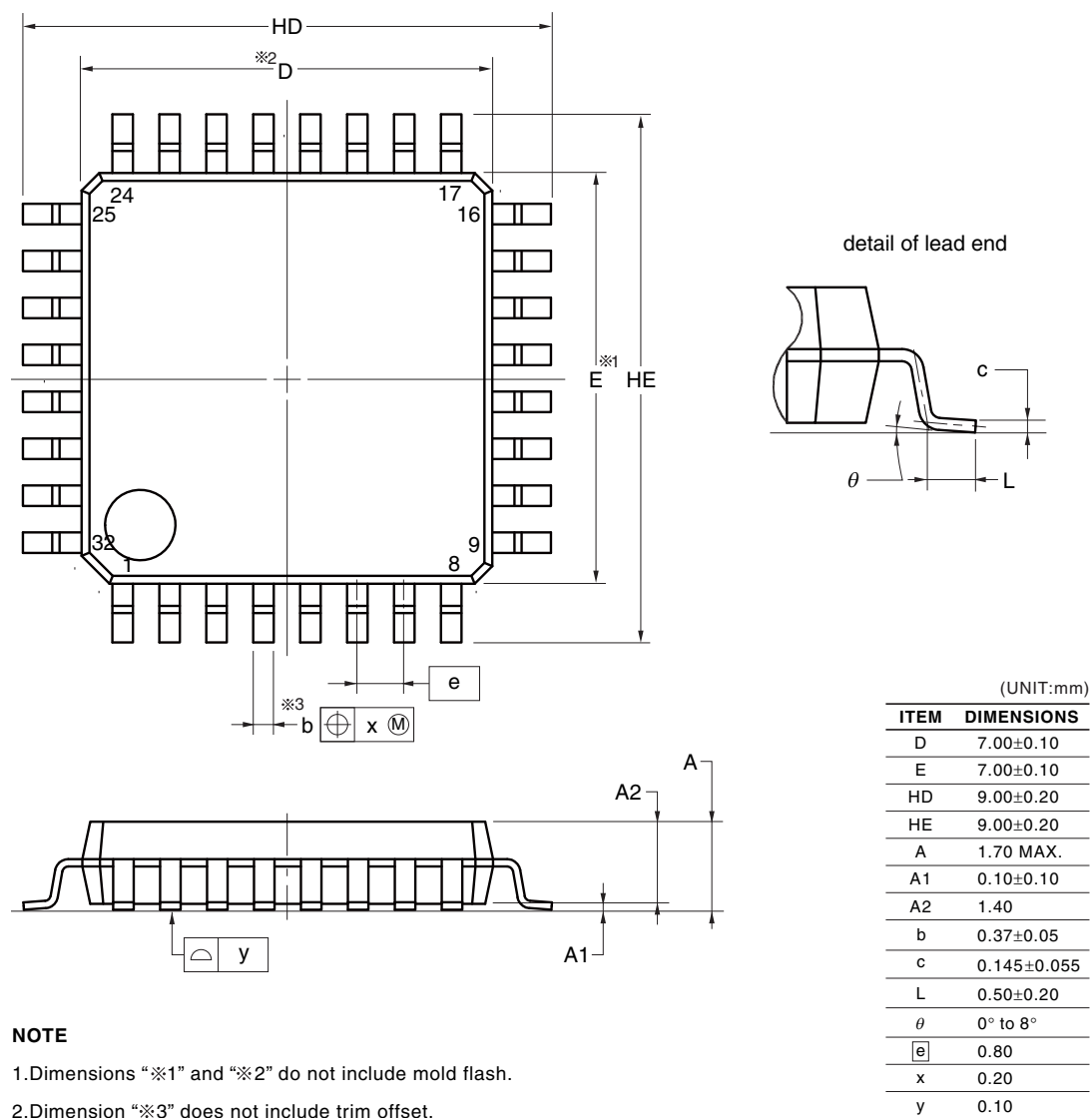
Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Note 4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

R5F104BAAFP, R5F104BCAFP, R5F104BDAFP, R5F104BEAFP, R5F104BFAFP, R5F104BGAFP
 R5F104BADFP, R5F104BCDFP, R5F104BDDFP, R5F104BEDFP, R5F104BFDFP, R5F104BGDFP
 R5F104BAGFP, R5F104BCGFP, R5F104BDGFP, R5F104BEGFP, R5F104BFGFP, R5F104BGGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2

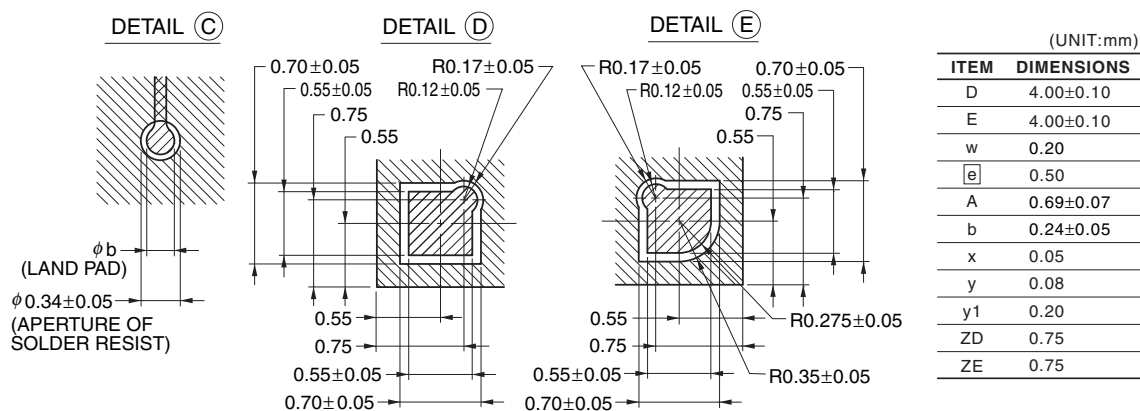
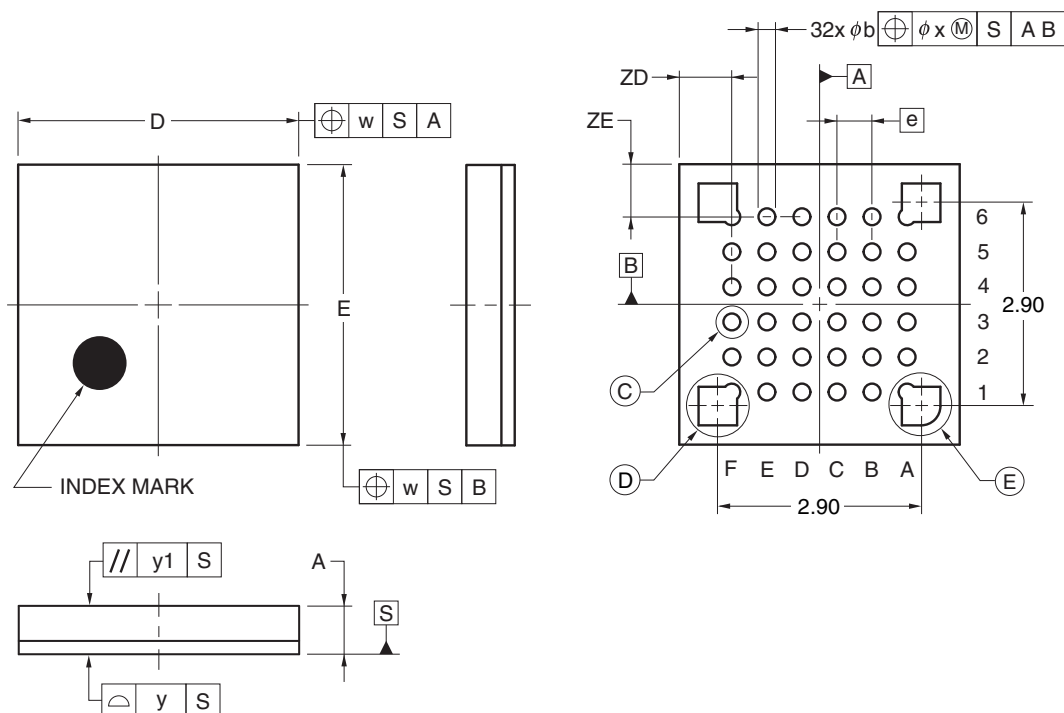


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4.3 36-pin products

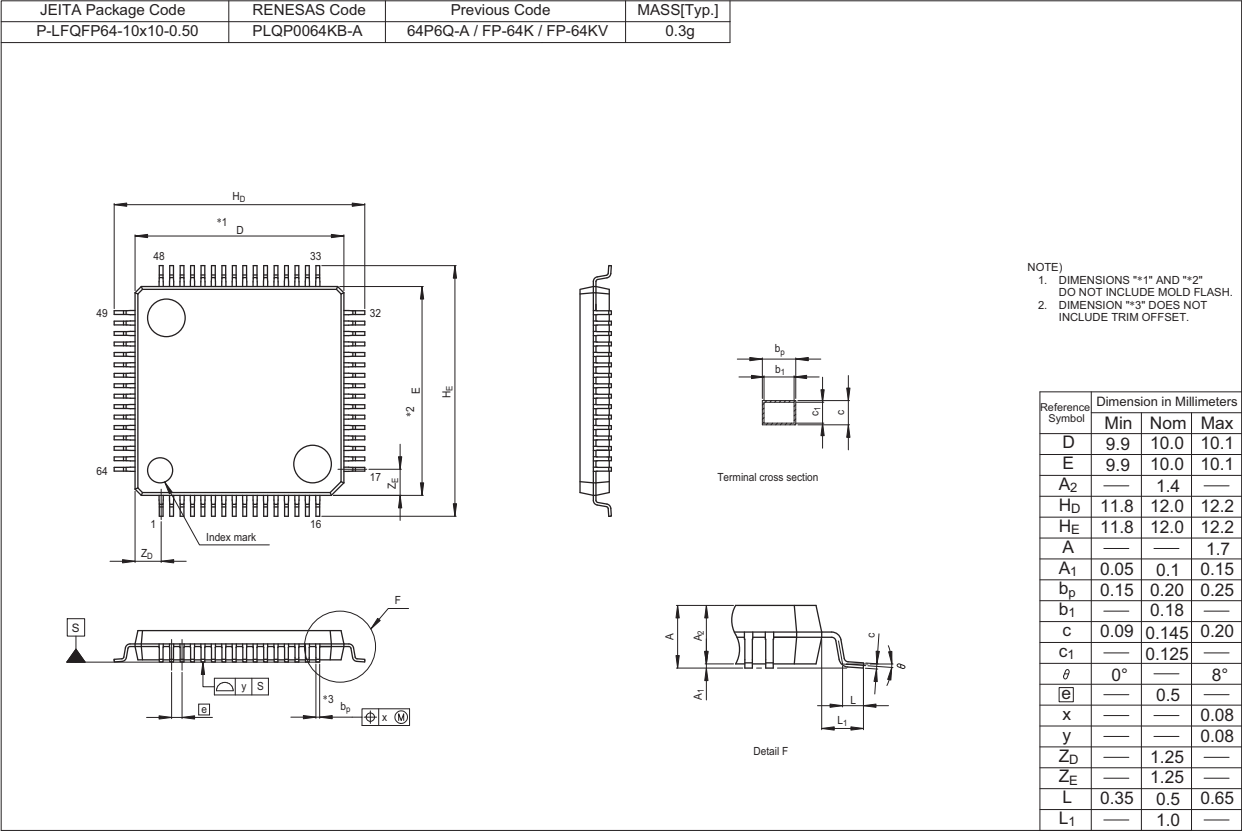
R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



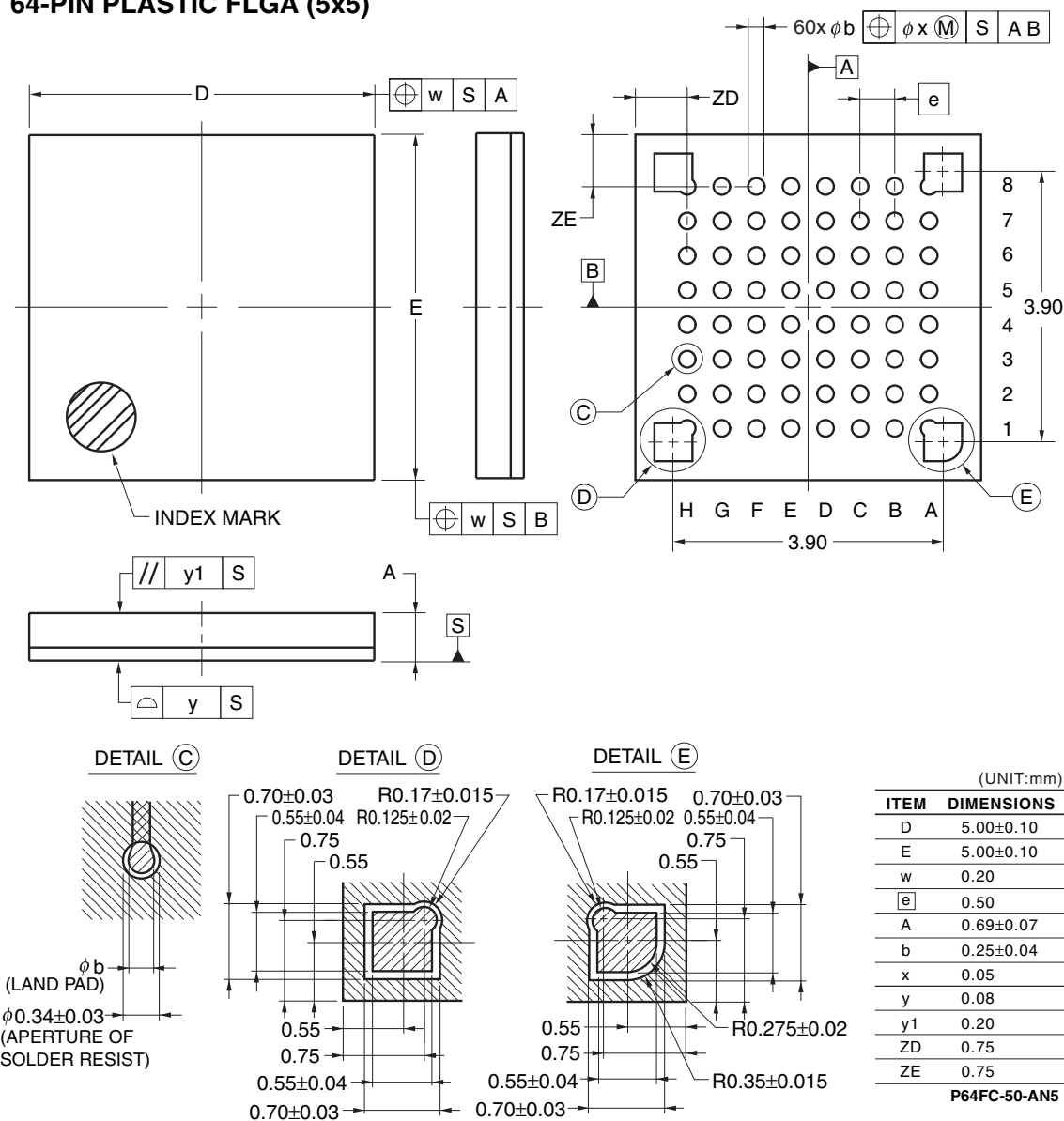
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R5F104LKAFB, R5F104LLAFB
R5F104LKGFB, R5F104LLGFB



R5F104LCALA, R5F104LDALA, R5F104LEALA, R5F104LFALA, R5F104LGALA, R5F104LHALA, R5F104LJALA
 R5F104LKALA, R5F104LLALA
 R5F104LCGLA, R5F104LDGLA, R5F104LEGLA, R5F104LFGLA, R5F104LGGLA, R5F104LHGLA, R5F104LJGLA
 R5F104LKGLA, R5F104LLGLA

64-PIN PLASTIC FLGA (5x5)



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